

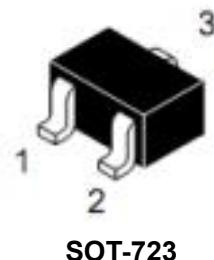
SSCN3904GS9

NPN Switching Transistor

➤ Features

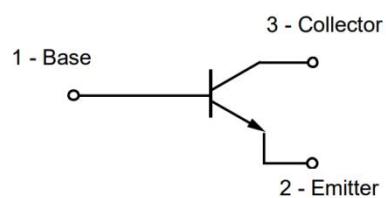
VCB	VCE	VBE	VCESAT	IC
60V	40V	6V	300mV	200mA

➤ Pin configuration



➤ Description

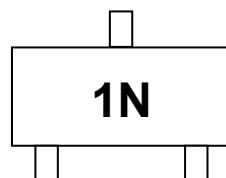
The NPN Transistor is designed for use in linear and switching applications. The device is housed in the SOT-723 package, which is designed for telephony and professional communication equipment.



➤ Applications

- General purpose switching and amplification
- Telephony and professional communication equipment

Circuit Diagram



Marking(Top View)

➤ Ordering Information

Device	Package	Shipping
SSCN3904GS9	SOT-723	8000/Reel

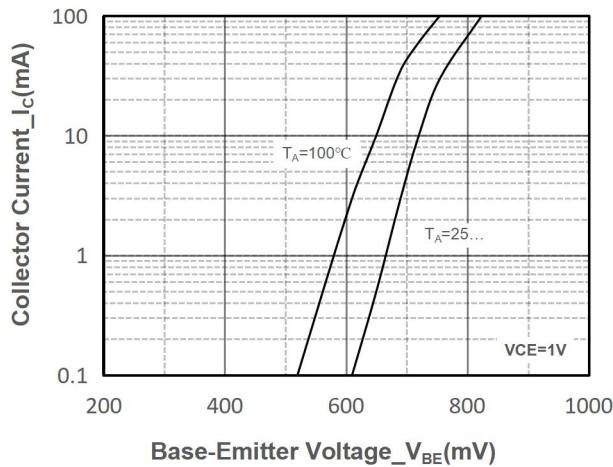
➤ **Absolute Maximum Ratings($T_A=25^\circ C$ unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector- Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current-Continuous	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$

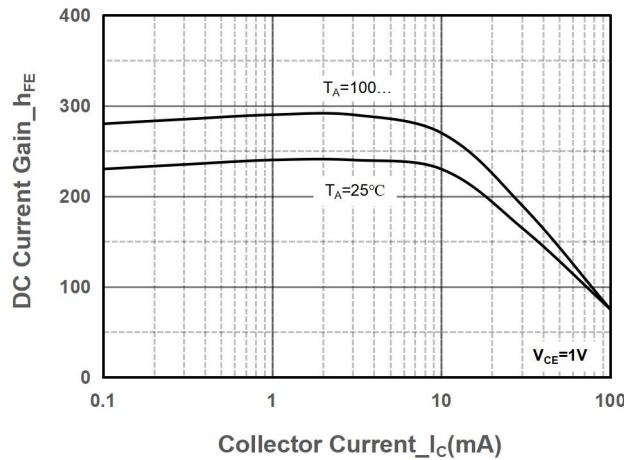
➤ **Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=10\mu A, I_E=0$	60			V
Collector-emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA, I_B=0$	40			V
Emitter -Base Breakdown Voltage	BV_{EBO}	$I_E=10\mu A, I_C=0$	6			V
Collector Cutoff Current	I_{CEX}	$V_{CE}=30V, V_{EB}=3V$			50	nA
Collector Cutoff Current	I_{CBO}	$V_{CB}=30V, I_E=0$			100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=3V, I_C=0$			100	nA
DC Current Gain	h_{FE}	$V_{CE}=1V, I_C=10mA$	100		300	
		$V_{CE}=1V, I_C=0.1mA$	40			
		$V_{CE}=1V, I_C=100mA$	30			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=5mA$			0.95	V
Transition frequency	f_T	$V_{CE}=20V, I_C=10mA$ $f=100MHz$	250			MHz
Delay Time	t_d	$V_{CC}=3V, V_{BE(off)}=-0.5V$ $I_C=10mA, I_{B1}=1mA$			35	ns
Rise Time	t_r	$V_{CC}=3V, V_{BE(off)}=-0.5V$ $I_C=10mA, I_{B1}=1mA$			35	ns
Storage Time	t_s	$V_{CC}=3V, I_C=10mA$ $I_{B1}= I_{B2}=1mA$			200	ns
Fall Time	t_f	$V_{CC}=3V, I_C=10mA$ $I_{B1}= I_{B2}=1mA$			50	ns

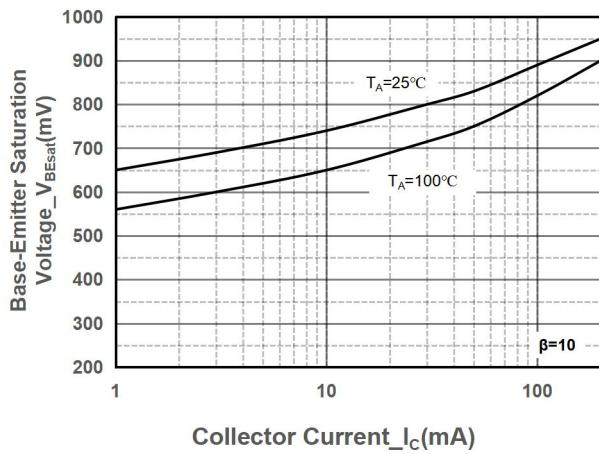
➤ **Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)**



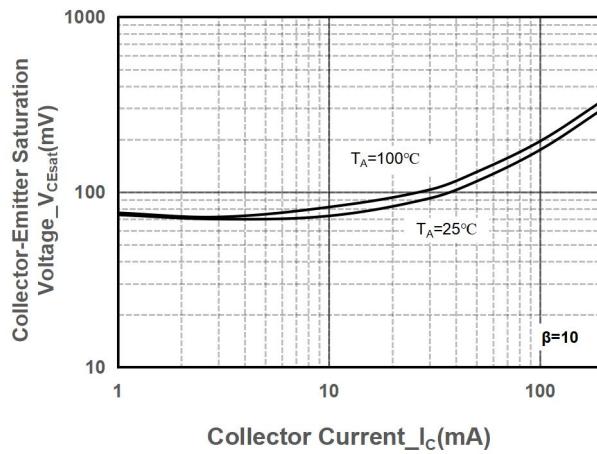
Collector Current vs. Base-Emitter Voltage



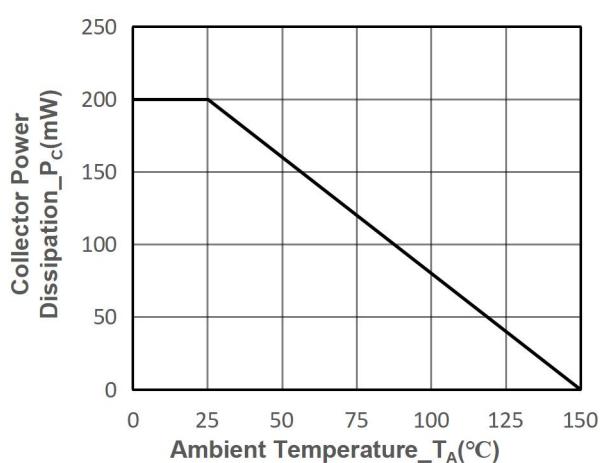
DC Current Gain vs. Collector Current



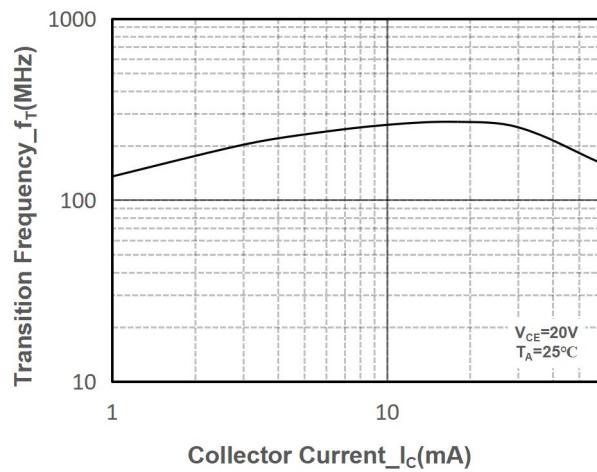
$V_{BE(sat)}$ vs. Collector Current



$V_{CE(sat)}$ vs. Collector Current

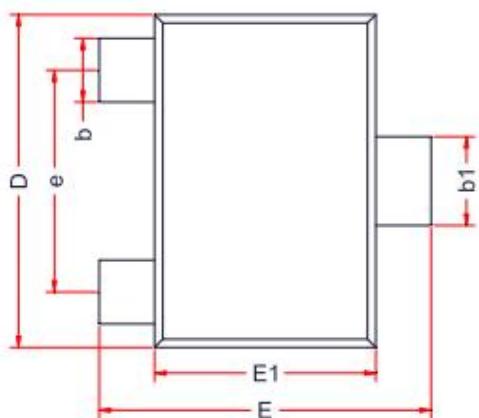
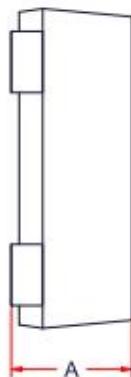
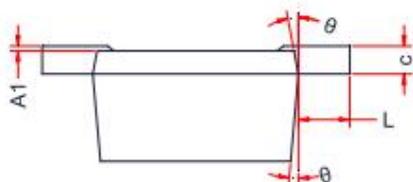


Power derating vs. Ambient temperature



Transition Frequency vs. Collector Current

- **Package Information**

SOT-723

TOP VIEW

SIDE VIEW

SIDE VIEW

DIM	Millimeters	
	Min.	Max.
A	0.43	0.55
A1	0.00	0.05
b	0.15	0.28
b1	0.22	0.37
c	0.075	0.18
D	1.15	1.25
E	1.15	1.25
E1	0.75	0.85
e	0.80Ref.	
L	0.12	0.28
θ	8°Ref.	

**DISCLAIMER**

SSCSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. SSCSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.

OUR PRODUCT SPECIFICATIONS ARE ONLY VALID IF OBTAINED THROUGH THE COMPANY'S OFFICIAL WEBSITE, CRM SYSTEM, OR OUR SALES PERSONNEL CHANNELS. IF CHANGES OR SPECIAL VERSIONS ARE INVOLVED, THEY MUST BE STAMPED WITH A QUALITY SEAL AND MARKED WITH A SPECIAL VERSION NUMBER TO BE VALID.